Low-power configurable multiple function gate Rev. 6 — 10 January 2011 P

Product data sheet

General description 1.

The 74AUP1G97 provides configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions MUX, AND, OR, NAND, NOR, inverter and buffer. All inputs can be connected to V_{CC} or GND.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74AUP1G97 has Schmitt trigger inputs making it capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
 - HBM JESD22-A114F exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power configurable multiple function gate

3. Ordering information

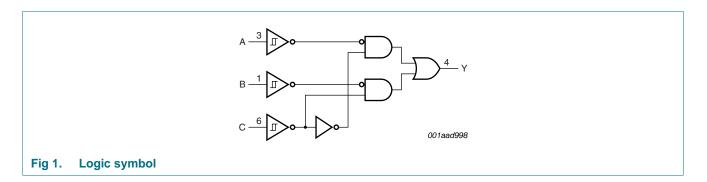
Table 1. Ordering information										
Type number	Package									
	Temperature range Name		Description	Version						
74AUP1G97GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363						
74AUP1G97GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886						
74AUP1G97GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891						
74AUP1G97GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115						
74AUP1G97GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202						

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP1G97GW	aV
74AUP1G97GM	aV
74AUP1G97GF	aV
74AUP1G97GN	aV
74AUP1G97GS	aV

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

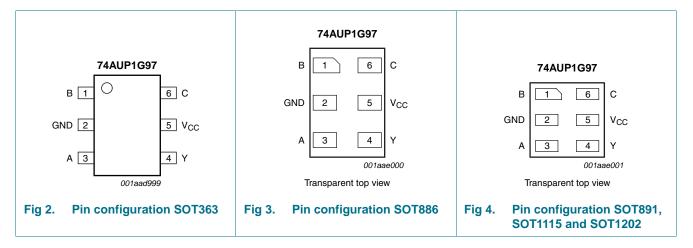
5. Functional diagram



Low-power configurable multiple function gate

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input
GND	2	ground (0 V)
A	3	data input
Y	4	data output
V _{CC}	5	supply voltage
С	6	data input

7. Functional description

Table 4. Function table^[1] Input Output С в Υ Α L L L L L L Н L Н L Н L L Н Н Н Н L L L Н L Н Н Н Н L L н н Н Н

[1] H = HIGH voltage level;

L = LOW voltage level.

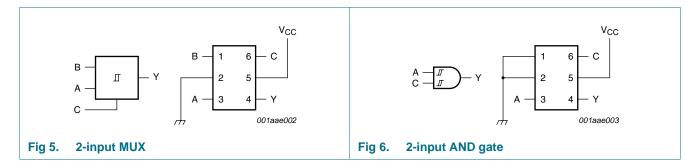
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Low-power configurable multiple function gate

7.1 Logic configurations

Table 5.Function selection table

Logic function	Figure
2-input MUX	see Figure 5
2-input AND	see Figure 6
2-input OR with one input inverted	see Figure 7
2-input NAND with one input inverted	see Figure 7
2-input AND with one input inverted	see Figure 8
2-input NOR with one input inverted	see Figure 8
2-input OR	see Figure 9
Inverter	see Figure 10
Buffer	see Figure 11



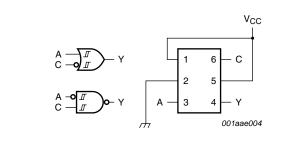


Fig 7. 2-input NAND gate with input A inverted or 2-input OR gate with input C inverted

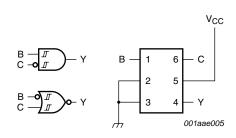
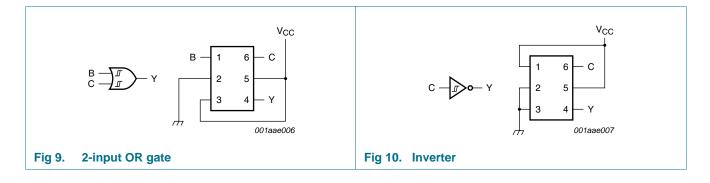
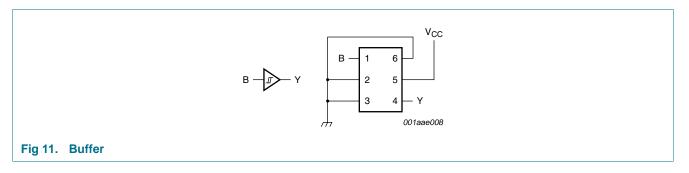


Fig 8. 2-input NOR gate with input B inverted or 2-input AND gate with input C inverted



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Limiting values 8.

Table 6. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
Ι _{ΟΚ}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[1] -0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[2]	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 $^\circ\text{C}$ the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

Recommended operating conditions 9.

	Recommended operating com				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C

Table 7 Recommended operating conditions

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10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = 2	5 °C					
√ _{ОН}	HIGH-level output voltage	$V_{I} = V_{T+} \text{ or } V_{T-}$				
		I_{O} = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7$ mA; $V_{CC} = 3.0$ V	2.72	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
√ _{OL}	LOW-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		I_{O} = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μA
OFF	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V	-	-	±0.2	μA
Δl _{OFF}	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
сс	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μA
∆l _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	<u>[1]</u> -	-	40	μA
CI	input capacitance	$V_{CC} = 0 V$ to 3.6 V; $V_{I} = GND$ or V_{CC}	-	1.1	-	pF
C _O	output capacitance	$V_0 = GND; V_{CC} = 0 V$	-	1.7	-	pF
	40 °C to +85 °C					•
V _{OH}	HIGH-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		$I_0 = -20 \ \mu\text{A}; \ V_{CC} = 0.8 \ \text{V} \text{ to } 3.6 \ \text{V}$	$V_{CC} - 0.1$	-	-	V
		$I_0 = -1.1 \text{ mA; } V_{CC} = 1.1 \text{ V}$	0.7V _{CC}	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_0 = -1.9 \text{ mA; } V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{\rm O} = -2.3 \text{ mA; } V_{\rm CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{\rm O} = -3.1 \text{ mA}; V_{\rm CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
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Symbol	Parameter	Conditions	Min	Тур	Max	Uni
V _{OL}	LOW-level output voltage	$V_1 = V_{T+}$ or V_{T-}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I_{O} = 1.1 mA; V_{CC} = 1.1 V	-	-	$0.3V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.37	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_0 = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μA
ΔI_{OFF}	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
Δl _{CC}	additional supply current		<u>[1]</u> -	-	50	μΑ
T _{amb} = -	40 °C to +125 °C					
V _{OH}	HIGH-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		I_{O} = –20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.6V _{CC}	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_1 = V_{T+} \text{ or } V_{T-}$				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33V _{CC}	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
lı	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μA
I _{OFF}	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V	-		±0.75	μΑ

Table 8. Static characteristics ...continued

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	1.4	μA
ΔI_{CC}	additional supply current		<u>[1]</u> -	-	75	μΑ

Table 8. Static characteristics ...continued

[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 13.

Symbol	Parameter	Conditions			25 °C		–40 °C to +125 °C			Unit
			I	Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pF	F									
t _{pd}	propagation delay	A, B, C to Y; see Figure 12	[2]							
		$V_{CC} = 0.8 V$		-	23.0	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		2.8	6.6	12.6	2.5	13.0	13.2	ns
		V_{CC} = 1.4 V to 1.6 V		2.3	4.7	7.6	2.5	8.2	8.6	ns
		V_{CC} = 1.65 V to 1.95 V		2.2	3.9	6.2	2.0	6.8	7.2	ns
		V_{CC} = 2.3 V to 2.7 V		2.0	3.2	4.5	1.7	5.1	5.3	ns
		V_{CC} = 3.0 V to 3.6 V		1.9	2.9	3.9	1.5	4.1	4.3	ns
C _L = 10 p	ρF									
t _{pd}	propagation delay	A, B, C to Y; see Figure 12	[2]							
		$V_{CC} = 0.8 V$		-	26.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.2	7.4	14.3	2.9	14.9	15.2	ns
		V_{CC} = 1.4 V to 1.6 V		2.6	5.3	8.7	2.8	9.4	9.8	ns
		V_{CC} = 1.65 V to 1.95 V		2.5	4.5	7.0	2.3	7.8	8.2	ns
		V_{CC} = 2.3 V to 2.7 V		2.4	3.7	5.2	2.1	5.9	6.1	ns
		V_{CC} = 3.0 V to 3.6 V		2.3	3.4	4.6	1.9	4.9	5.1	ns
C _L = 15 p	٥F									
t _{pd}	propagation delay	A, B, C to Y; see Figure 12	[2]							
		$V_{CC} = 0.8 V$		-	30.1	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		3.6	8.2	16.0	3.2	16.7	17.0	ns
		V_{CC} = 1.4 V to 1.6 V		2.9	5.9	9.6	3.1	10.4	10.9	ns
		V_{CC} = 1.65 V to 1.95 V		2.8	5.0	7.8	2.5	8.7	9.1	ns
		V_{CC} = 2.3 V to 2.7 V		2.7	4.2	5.8	2.4	6.5	6.9	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.5	3.8	5.1	2.2	5.5	5.7	ns

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Symbol	Parameter	Conditions		25 °C			-4	0 °C to +1	25 °C	Unit
				Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 30	pF									
t _{pd}	propagation delay	A, B, C to Y; see Figure 12	[2]							
		$V_{CC} = 0.8 V$		-	38.3	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		4.6	10.5	20.9	4.0	21.8	22.2	ns
		V_{CC} = 1.4 V to 1.6 V		3.7	7.4	12.2	3.8	13.3	14.0	ns
		V_{CC} = 1.65 V to 1.95 V		3.5	6.3	9.9	3.2	11.1	11.8	ns
		V_{CC} = 2.3 V to 2.7 V		3.4	5.3	7.4	3.1	8.3	8.8	ns
		V_{CC} = 3.0 V to 3.6 V		3.2	4.9	6.6	2.8	7.0	7.4	ns
C _L = 5 p	F, 10 pF, 15 pF and	30 pF								
C _{PD}	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	<u>[3]</u>							
	capacitance	$V_{CC} = 0.8 V$		-	2.6	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V		-	2.8	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V		-	2.9	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V		-	3.1	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	3.7	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	4.3	-	-	-	-	рF

Table 9. Dynamic characteristics ... continued

0 V): for tost circuit soo Figure 12

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}{}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}{}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching; $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

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12. Waveforms

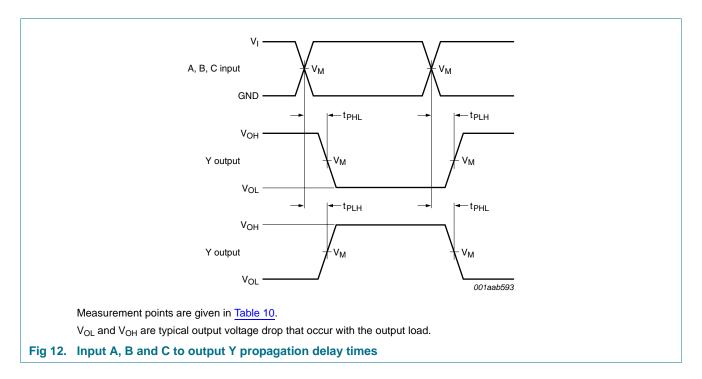


Table 10. Measurement points

Supply voltage	Output	Input				
V _{cc}	V _M	V _M	VI	t _r = t _f		
0.8 V to 3.6 V	0.5V _{CC}	0.5V _{CC}	V _{CC}	≤ 3.0 ns		

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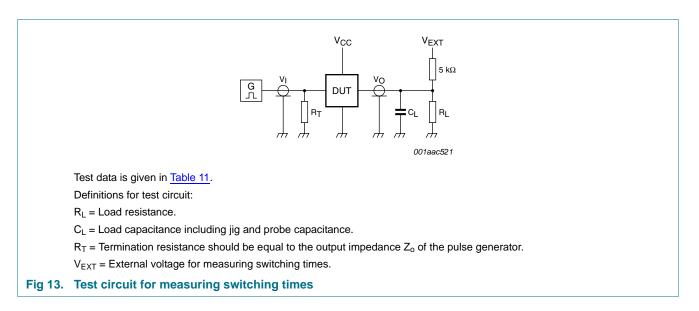


Table 11. Test data

Supply voltage	Load		V _{EXT}		
V _{cc}	CL	RL ^[1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	2V _{CC}

[1] For measuring enable and disable times $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 M\Omega$.

13. Transfer characteristics

Table 12. Transfer characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 13.

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Тур	Мах	Min	Max (85 °C)	Max (125 °C)	
	positive-going	see Figure 14 and Figure 15							
	threshold voltage	$V_{CC} = 0.8 V$	0.30	-	0.60	0.30	0.60	0.62	V
		$V_{CC} = 1.1 V$	0.53	-	0.90	0.53	0.90	0.92	V
		V _{CC} = 1.4 V	0.74	-	1.11	0.74	1.11	1.13	V
		V _{CC} = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		$V_{CC} = 2.3 V$	1.37	-	1.77	1.37	1.77	1.80	V
		$V_{CC} = 3.0 V$	1.88	-	2.29	1.88	2.29	2.32	V
V _{T-}	negative-going threshold voltage	see Figure 14 and Figure 15							
		$V_{CC} = 0.8 V$	0.10	-	0.60	0.10	0.60	0.60	V
		V _{CC} = 1.1 V	0.26	-	0.65	0.26	0.65	0.65	V
		$V_{CC} = 1.4 V$	0.39	-	0.75	0.39	0.75	0.75	V
		V _{CC} = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
		$V_{CC} = 2.3 V$	0.69	-	1.04	0.69	1.04	1.04	V
		$V_{CC} = 3.0 V$	0.88	-	1.24	0.88	1.24	1.24	V

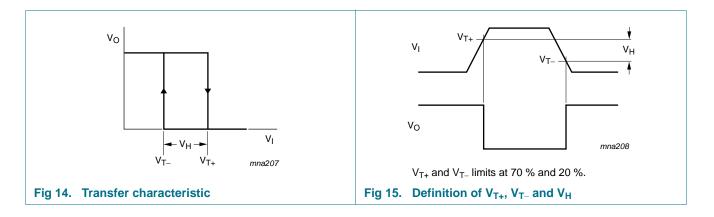
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Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		
			Min	Тур	Мах	Min	Max (85 °C)	Max (125 °C)	
V _H hysteresis voltage	,	$(V_{T+} - V_{T-})$; see Figure 14, Figure 15, Figure 16 and Figure 17						'	
		$V_{CC} = 0.8 V$	0.07	-	0.50	0.07	0.50	0.50	V
		V _{CC} = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V
		$V_{CC} = 1.4 V$	0.18	-	0.56	0.18	0.56	0.56	V
		V _{CC} = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V
		$V_{CC} = 2.3 V$	0.53	-	0.92	0.53	0.92	0.92	V
		$V_{CC} = 3.0 V$	0.79	-	1.31	0.79	1.31	1.31	V

Table 12. Transfer characteristics ...continued

Voltages are referenced to GND (ground = 0 V; for test circuit see <u>Figure 13</u>.

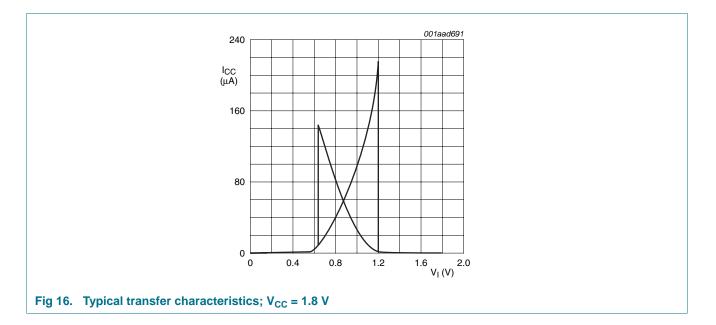
14. Waveforms transfer characteristics

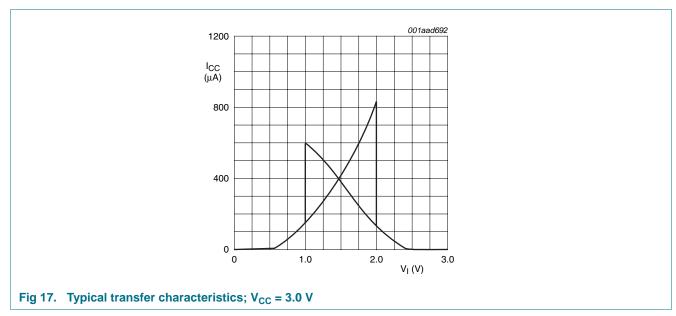


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15. Package outline

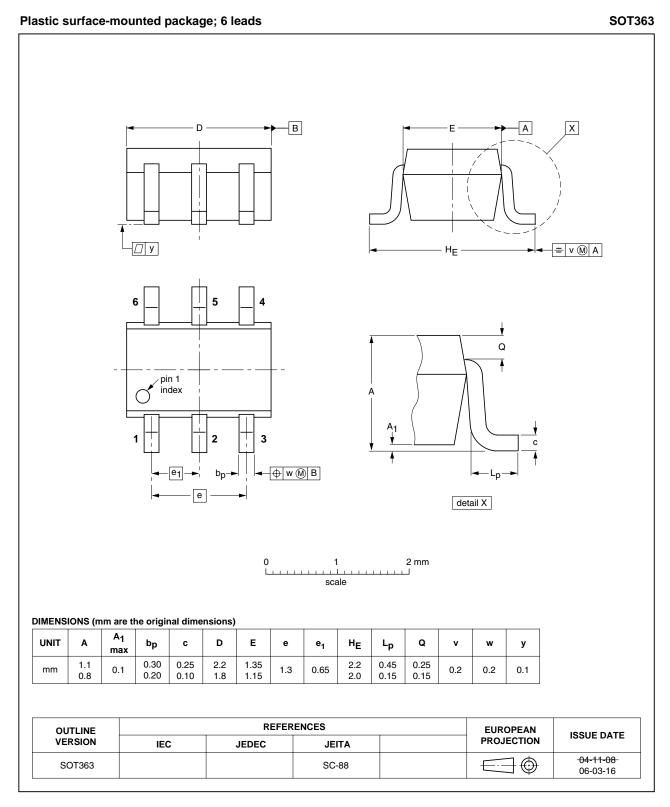
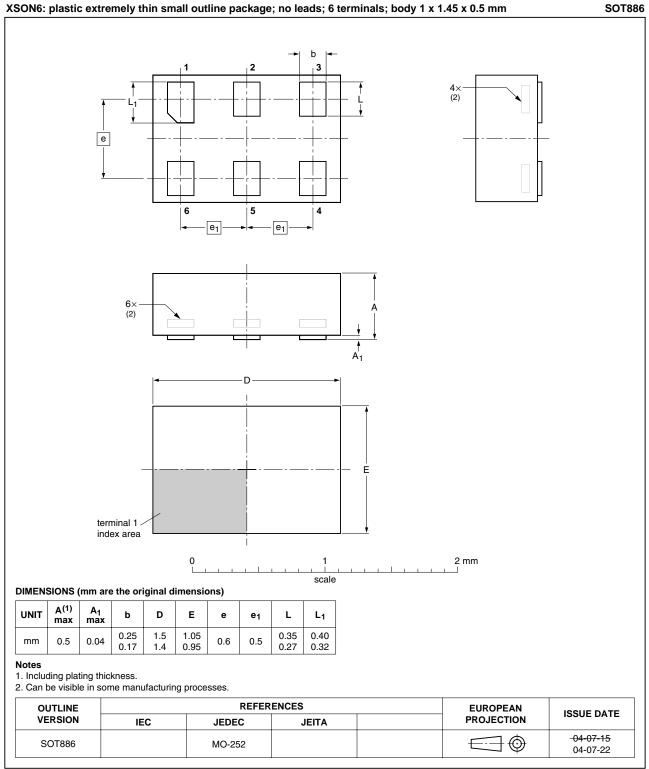


Fig 18. Package outline SOT363 (SC-88)

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XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

Fig 19. Package outline SOT886 (XSON6)

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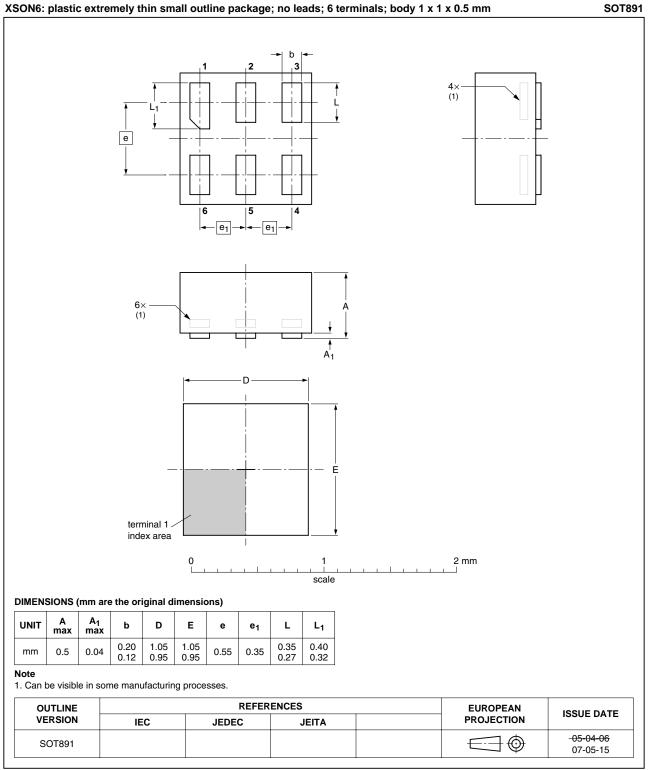
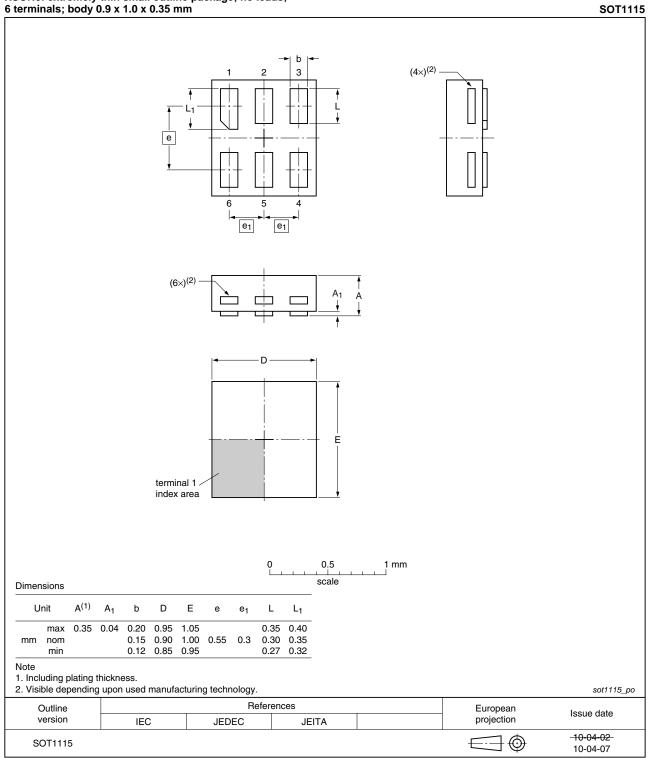


Fig 20. Package outline SOT891 (XSON6)

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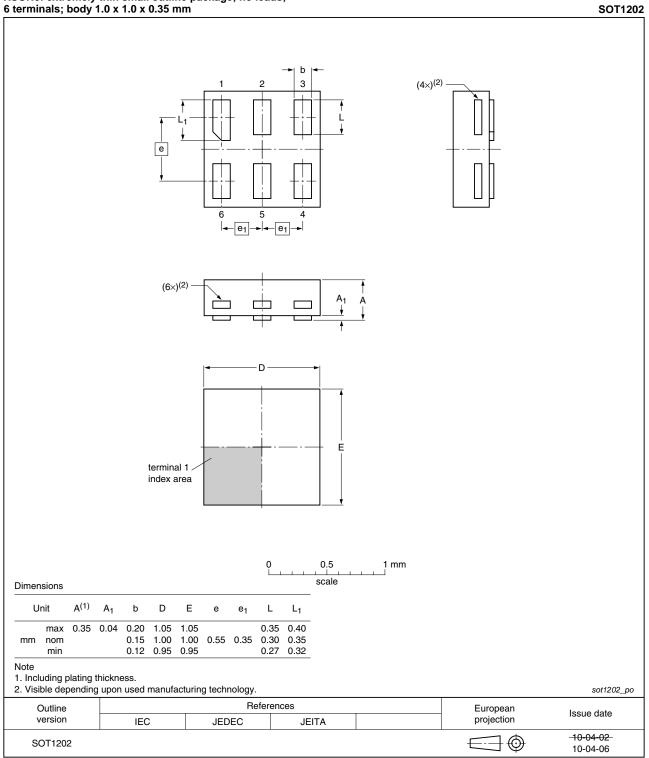


XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 21. Package outline SOT1115 (XSON6)

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 22. Package outline SOT1202 (XSON6)

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16. Abbreviations

Table 13. Ab	previations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

17. Revision history

Table 14. Revision history **Document ID Release date** Data sheet status Change notice Supersedes 74AUP1G97 v.6 20110110 Product data sheet 74AUP1G97 v.5 Modifications: • Schmitt trigger symbol added to functional drawings. 74AUP1G97 v.5 20101020 Product data sheet 74AUP1G97 v.4 Modifications: • Added type number 74AUP1G97GN (SOT1115/XSON6 package). Added type number 74AUP1G97GS (SOT1202/XSON6 package). 74AUP1G97 v.4 20090623 Product data sheet -74AUP1G97 v.3 74AUP1G97 v.3 20090518 Product data sheet -74AUP1G97 v.2 74AUP1G97 v.2 Product data sheet 74AUP1G97 v.1 20090327 -74AUP1G97 v.1 Product data sheet 20061107 _ -

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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